BC847RAPN

45 V, 100 mA NPN/PNP general-purpose double transistors

14 September 2018 **Product data sheet**

1. General description

NPN/PNP general-purpose double transistors in a leadless ultra small DFN1412-6 (SOT1268) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: BC847RA

PNP/PNP complement: BC857RA

2. Features and benefits

- Reduces component count
- Reduces pick and place costs
- Low package height of 0.5 mm
- AEC-Q101 qualified

3. Applications

- General-purpose switching and amplification
- Mobile applications

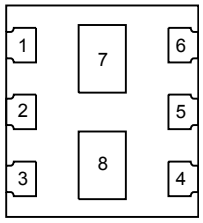
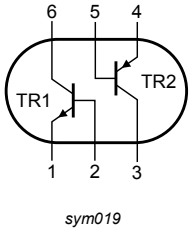
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity							
V_{CEO}	collector-emitter voltage	open base		-	-	45	V
I_C	collector current			-	-	100	mA
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	-	200	mA
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 2 mA; T_{amb} = 25 °C		200	-	450	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	 Transparent top view DFN1412-6 (SOT1268)	 sym019
2	B1	base TR1		
3	C2	collector TR2		
4	E2	emitter TR2		
5	B2	base TR2		
6	C1	collector TR1		
7	C1	collector TR1		
8	C2	collector TR2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC847RAPN	DFN1412-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm	SOT1268

7. Marking

Table 4. Marking codes

Type number	Marking code
BC847RAPN	A4

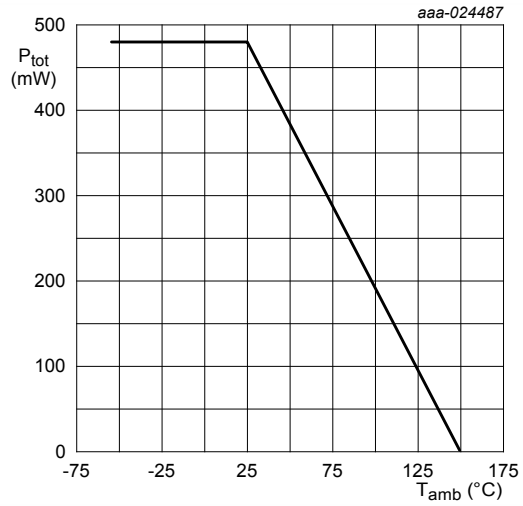
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	45	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
I_C	collector current			-	100	mA
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	200	mA
I_{BM}	peak base current			-	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	325	mW
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	480	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

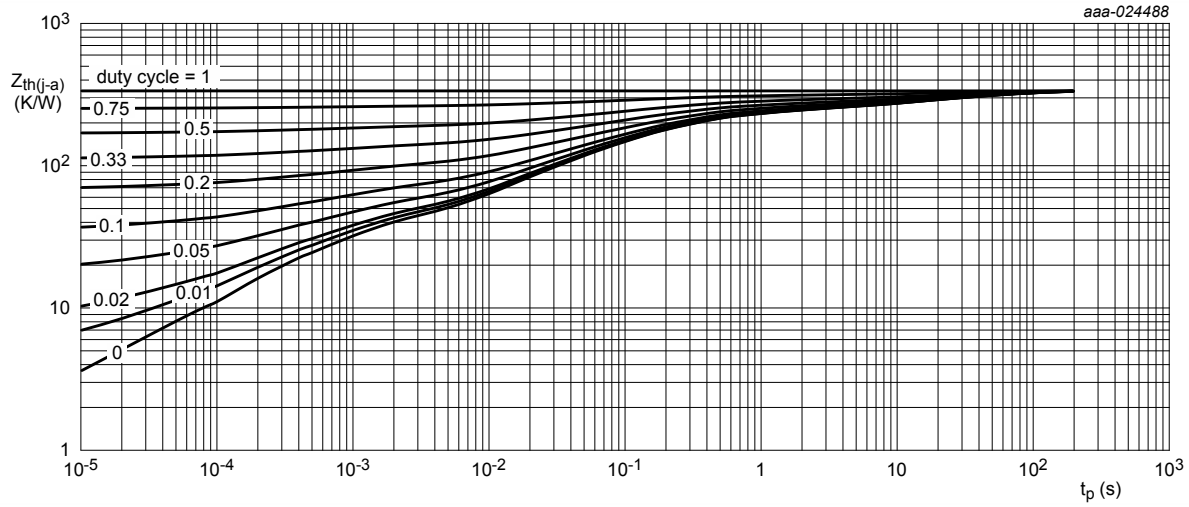
Fig. 1. Per device: Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	261	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



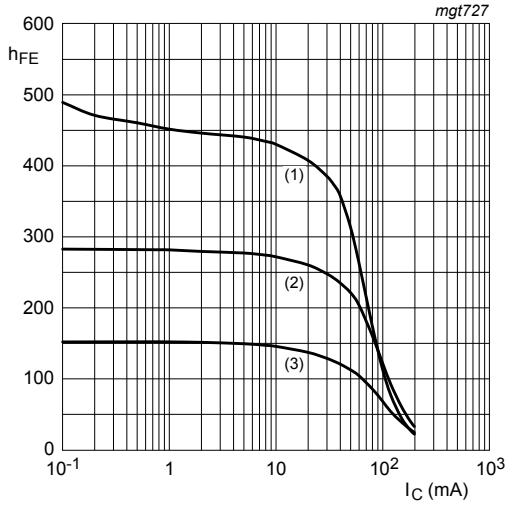
FR4 PCB, standard footprint

Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

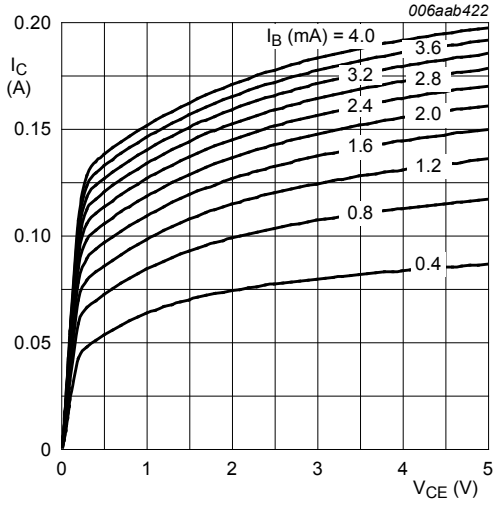
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity							
I_{CBO}	collector-base cut-off current	V_{CB} = 30 V; I_E = 0 A; T_{amb} = 25 °C		-	-	15	nA
		V_{CB} = 30 V; I_E = 0 A; T_j = 150 °C		-	-	5	µA
I_{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I_C = 0 A; T_{amb} = 25 °C		-	-	100	nA
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 2 mA; T_{amb} = 25 °C		200	-	450	
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C		-	-	100	mV
		I_C = 100 mA; I_B = 5 mA; T_{amb} = 25 °C		-	-	300	mV
V_{BEsat}	base-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C		-	760	-	mV
		I_C = 100 mA; I_B = 5 mA; T_{amb} = 25 °C		-	900	-	mV
V_{BE}	base-emitter voltage	V_{CE} = 5 V; I_C = 2 mA; T_{amb} = 25 °C		600	660	725	mV
		V_{CE} = 5 V; I_C = 10 mA; T_{amb} = 25 °C		-	710	820	mV
C_c	collector capacitance	V_{CB} = 10 V; I_E = 0 A; i_e = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	4	pF
C_e	emitter capacitance	V_{EB} = 0.5 V; I_C = 0 A; i_c = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	11	-	pF
		V_{EB} = -0.5 V; I_C = 0 mA; i_c = 0 mA; f = 1 MHz; T_{amb} = 25 °C		-	10	-	pF
f_T	transition frequency	V_{CE} = 5 V; I_C = 10 mA; f = 100 MHz; T_{amb} = 25 °C		100	-	-	MHz
NF	noise figure	V_{CE} = 5 V; I_C = 0.2 mA; R_S = 2 kΩ; f = 1 MHz; T_{amb} = 25 °C		-	-	10	dB



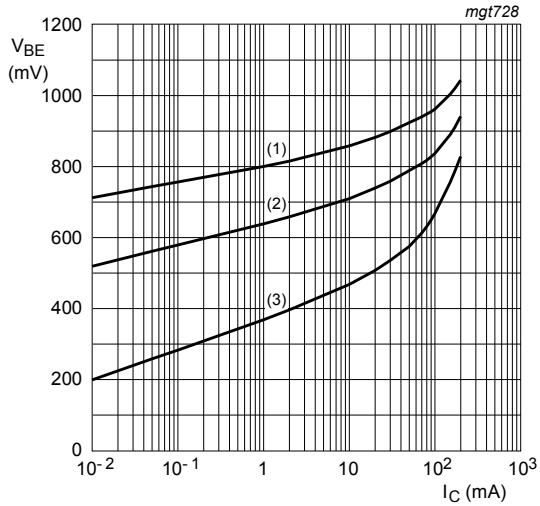
V_{CE} = 5 V
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = −55 °C

Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values



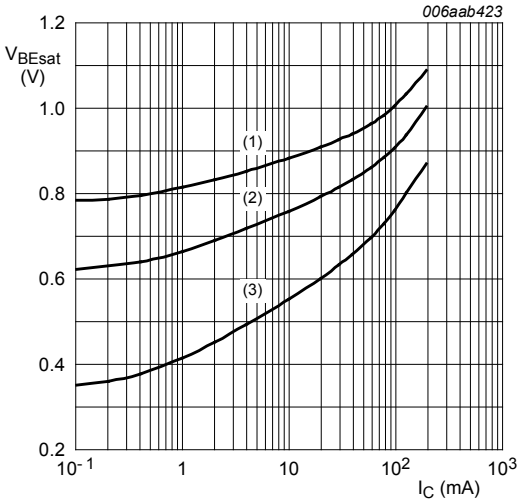
T_{amb} = 25 °C

Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



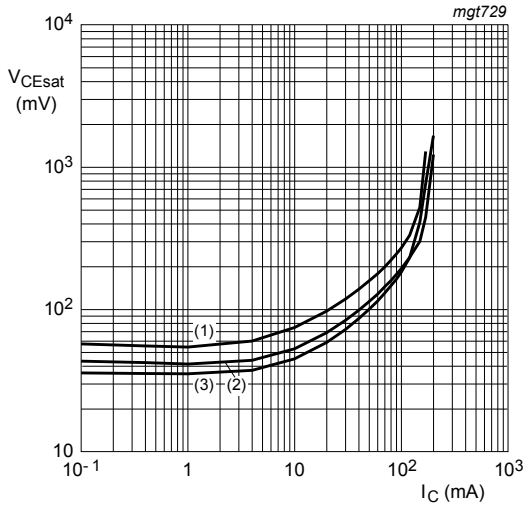
V_{CE} = 5 V
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Fig. 5. NPN transistor: Base-emitter voltage as a function of collector current; typical values



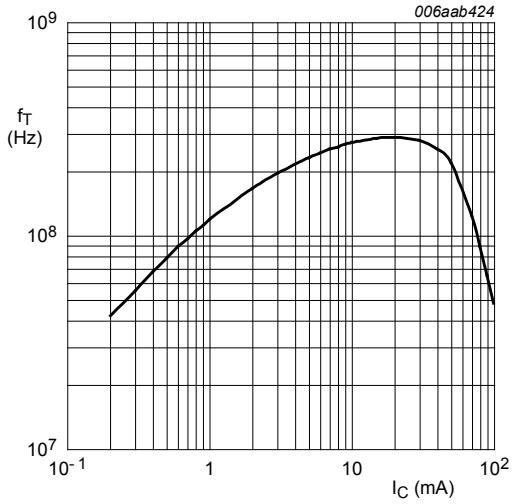
I_C/I_B = 20
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Fig. 6. NPN transistor: Base-emitter saturation voltage as a function of collector current; typical values



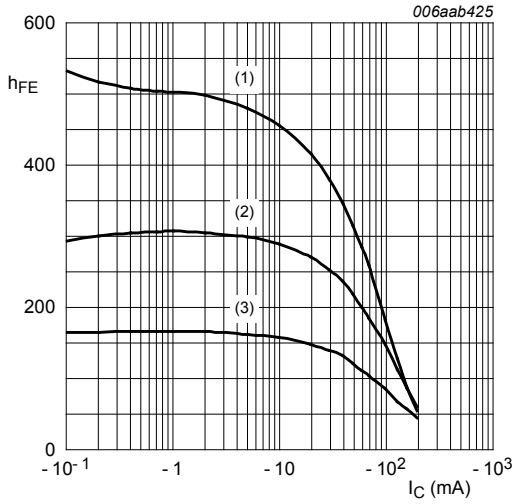
I_C/I_B = 20
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Fig. 7. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



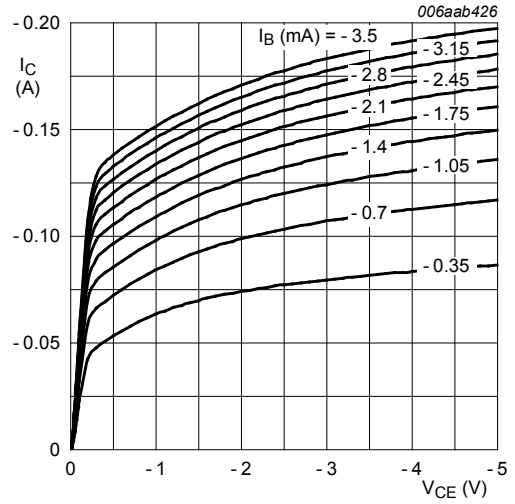
T_{amb} = 25 °C;
V_{CE} = 5 V;
f = 100 MHz

Fig. 8. NPN transistor: Transition frequency as a function of collector current; typical values



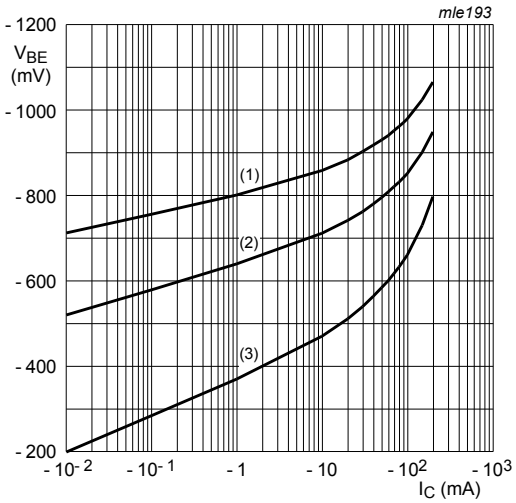
V_{CE} = -5 V
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = −55 °C

Fig. 9. PNP transistor: DC current gain as a function of collector current; typical values



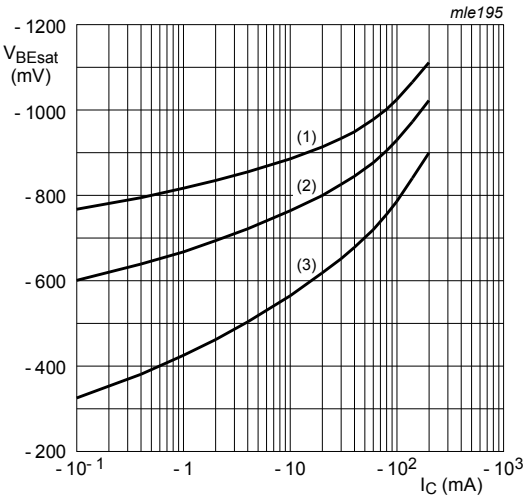
T_{amb} = 25 °C

Fig. 10. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



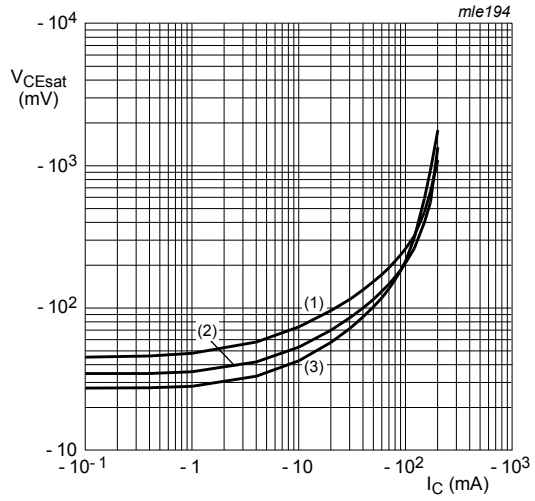
V_{CE} = -5 V
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Fig. 11. PNP transistor: Base-emitter voltage as a function of collector current; typical values



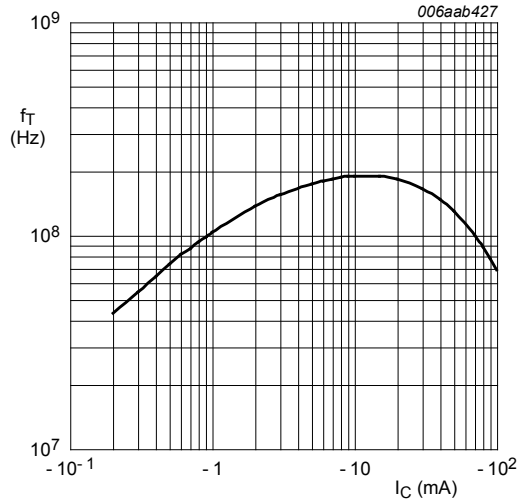
I_C/I_B = 20
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Fig. 12. PNP transistor: Base-emitter saturation voltage as a function of collector current; typical values



I_C/I_B = 20
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Fig. 13. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



T_{amb} = 25 °C;
V_{CE} = -5 V;
f = 100 MHz

Fig. 14. PNP transistor: Transition frequency as a function of collector current; typical values

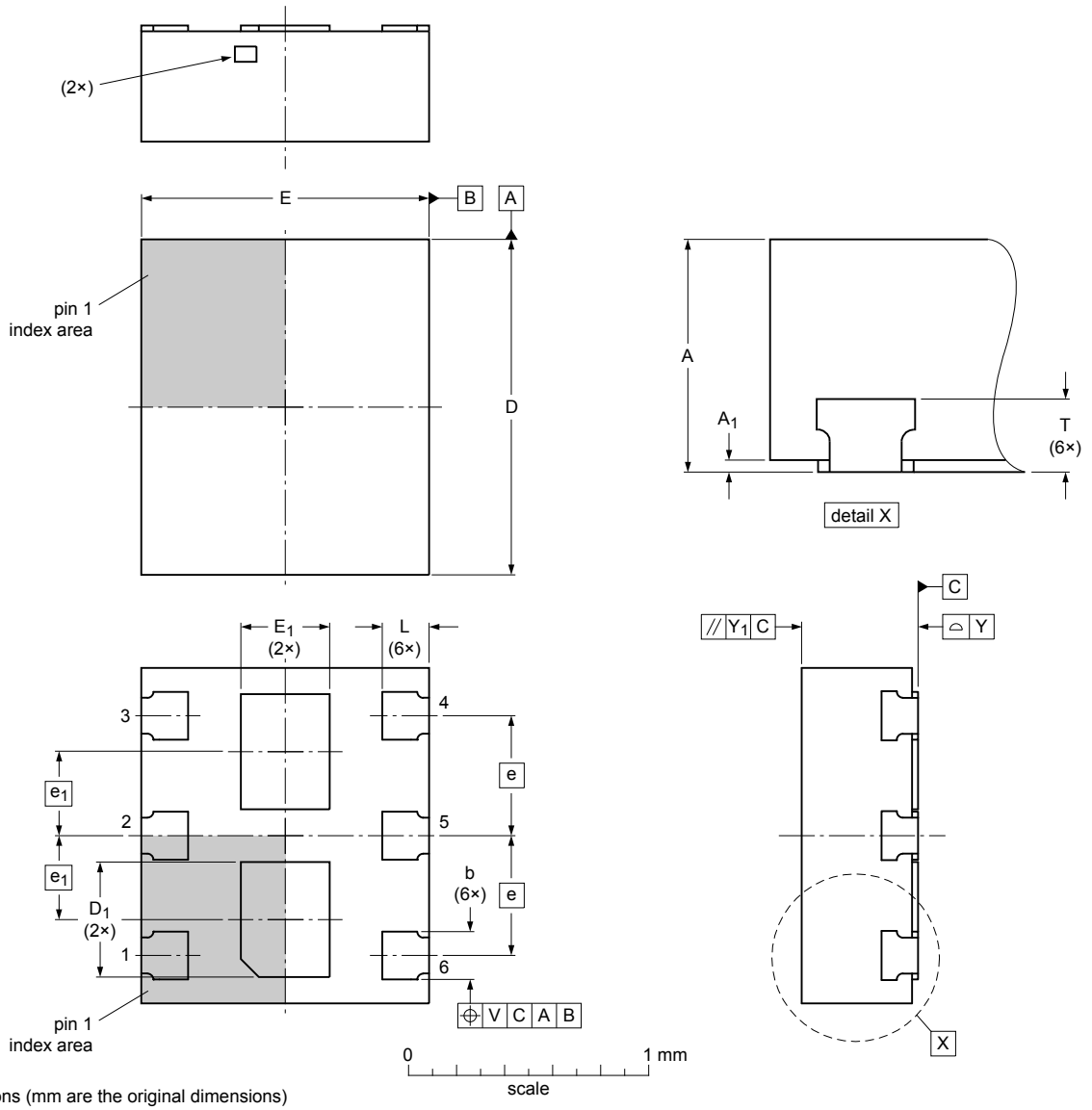
11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

DFN1412-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 x 1.2 x 0.47 mm **SOT1268**



Dimensions (mm are the original dimensions)

Unit[1]		A	A_1	b	D	D_1	E	E_1	e	e_1	L	T	V	Y	Y_1
mm	min	0.44	0.00	0.15	1.35	0.43	1.15	0.32			0.145	0.10			
	nom	0.47		0.20	1.40	0.48	1.20	0.37	0.5	0.35	0.195	0.16	0.1	0.05	0.05
	max	0.50	0.04	0.25	1.45	0.53	1.25	0.42			0.245	0.22			

Note
1. Dimension A is including plating thickness.

sot1268_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1268		- - -				~~18-08-23~~ 18-09-11

Fig. 15. Package outline DFN1412-6 (SOT1268)

13. Soldering

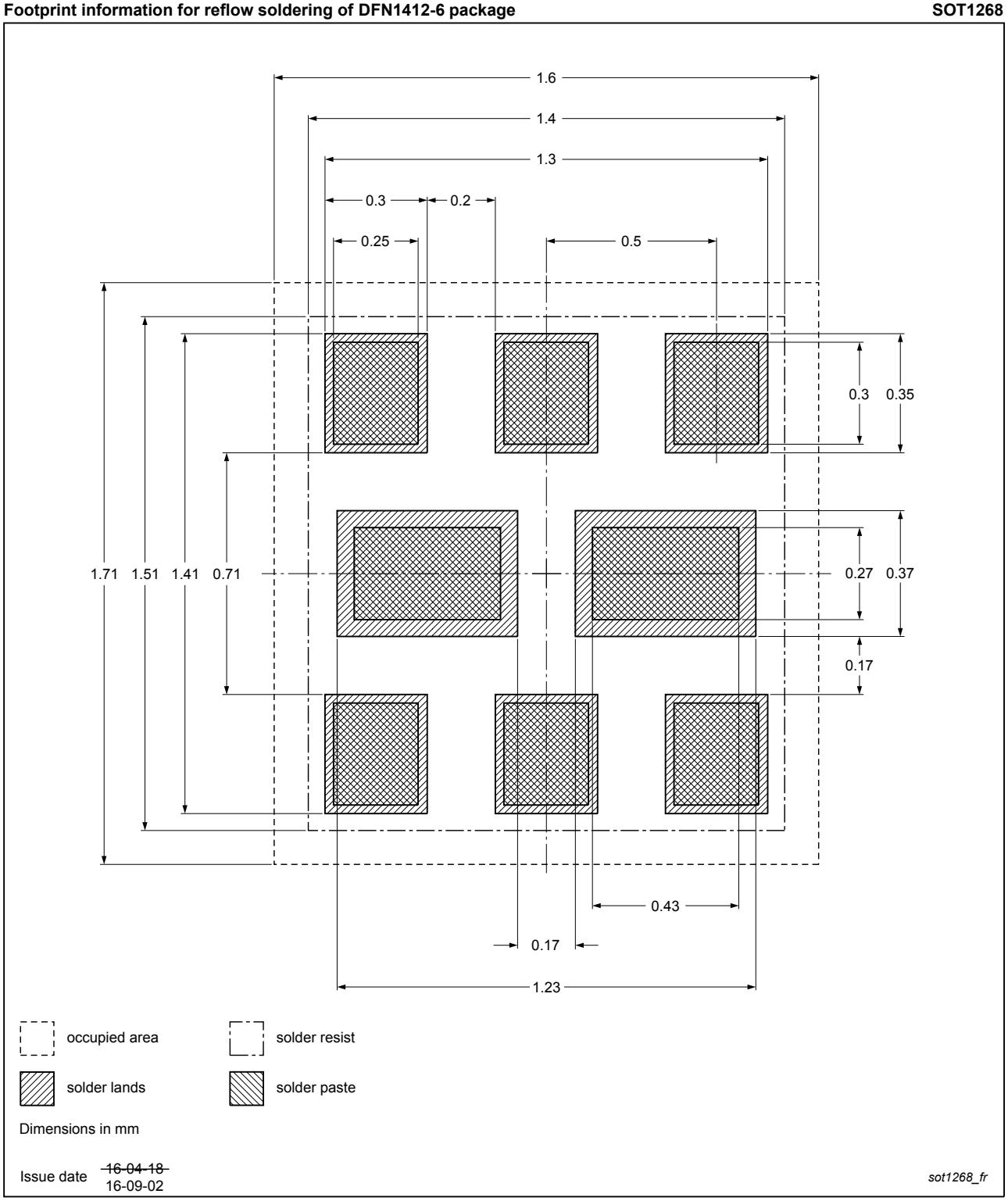


Fig. 16. Reflow soldering footprint for DFN1412-6 (SOT1268)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC847RAPN v.2	20180914	Product data sheet	-	BC847RAPN v.1
Modifications:	• Package outline drawing updated: Unit T added			
BC847RAPN v.1	20170607	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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Date of release: 14 September 2018

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